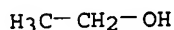


L15 ANSWER 10 OF 12 HCAPLUS COPYRIGHT 2003 ACS on STN
 AN 1999:796009 HCAPLUS
 DN 132:43779
 TI Forming a titanium-doped tantalum pentoxide layer
 IN Narwankar, Pravin K.; Sahin, Turgut; Urdahl, Randall S.; Velaga, Ankineedu; Liu, Patricia
 PA Applied Materials, Inc., USA
 SO PCT Int. Appl., 28 pp.
 CODEN: PIXXD2
 DT Patent
 LA English
 IC ICM C23C016-40
 CC 76-10 (Electric Phenomena)
 Section cross-reference(s): 75
 FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 9964643	A1	19991216	WO 1999-US13309	19990611
W: JP, KR				
RW: AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE				
US 6218300	B1	20010417	US 1998-97301	19980612
EP 1086259	A1	20010328	EP 1999-930229	19990611
R: BE, DE, GB, NL, IE				
US 1998-97301	A	19980612		
WO 1999-US13309	W	19990611		

AB A Ti-doped Ta₂O₅ dielec. layer is formed using a CVD process. A substrate is placed in a deposition chamber. A source of Ta, a source of Ti, and an O-contg. gas are then fed into the chamber. Thermal energy is used to decomp. the source of Ta to form Ta atoms and decomp. the source of Ti to form Ti atoms in the deposition chamber. The Ti atoms, Ta atoms, and the O-contg. gas then react to form a Ta₂O₅ dielec. film doped with Ti.
 ST titanium doped tantalum pentoxide layer formation; oxide tantalum titanium
 IT 6074-84-6, Pentaethoxytantalum 172901-22-3
 RL: NUU (Other use, unclassified); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)
 (forming a titanium-doped tantalum pentoxide layer by CVD using)
 RN 6074-84-6 HCAPLUS
 CN Ethanol, tantalum(5+) salt (9CI) (CA INDEX NAME)



1/5 Ta(V)

RN 172901-22-3 HCAPLUS
 CN Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-, (OC-6-23)- (9CI) (CA INDEX NAME)

